

KOREAN PATENT ABSTRACTS

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(54) **A Semiconductor Device having a transparent conductive layer and a Fabricating Method Thereof.**

(57)Abstract:

This invention relates to a fabricating method of forming a transparent conductive layer using electroless plating, a method of fabricating a pixel electrode of a thin film transistor, comprising the steps of: forming a photosensitization material pattern by a photolithography process to expose a lower substrate after a photosensitization material applied; forming a metal chelator material including a catalyst on a results; remaining the catalyst on a substrate and the photosensitization film pattern exposed by a accelerator process; and forming a conductive layer having a wanted thickness by depositing a designated metal on a results, so that it can prevent a special blazing fire.

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(72) 발명자	경기도 수원시 팔달구 매탄동 41번지 (우: 441-742) 황광희 서울특별시 송파구 오금동 71-1 손정하 서울특별시 송파구 잠실동 9구의 현대아파트 1306호

(54) 투옌노선택을 가지는 반도체상자의 제조방법

[illegible]

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